TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA4002F

VHF~UHF WIDE BAND AMPLIFIER

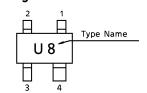
FEATURES

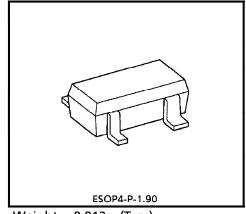
- Band Width 1.3GHz (Typ.) (3dB down)
- High Gain: $|S_{21}|^2 = 23dB$ (Typ.) (f = 500MHz)
- 50 Ω Input and Output Impedance
- Small Package

PIN ASSIGNMENT (TOP VIEW)



Marking





Weight: 0.013g (Typ.)

MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	6	V
Total Power Dissipation	P _D *	300	mW
Operating Temperature	T _{opr}	- 40∼85	°C
Storage Temperature	T _{stg}	- 55∼125	°C

When mounted glass epoxy of 2.5cm² x 1.6t

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

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CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT			
Circuit Current	lcc	_	$V_{CC} = 5V$, Non carrier	10	14	20	mA			
Insertion Gain	S ₂₁ ²	1	V _{CC} = 5V, f = 500MHz	20	23	26	dB			
Band Width	BW	1	V _{CC} = 5V (Note 1)	0.8	1.3	_	GHz			
Noise Figure	NF	1	V _{CC} = 5V, f = 500MHz	_	4.7	7	dB			
Input Return Loss	S ₁₁ ²	1	V _{CC} = 5V, f = 500MHz	_	-8	_	dB			
Output Return Loss	$ S_{22} ^2$	1	$V_{CC} = 5V$, $f = 500MHz$	_	– 15	_	dB			
Isolation	S ₁₂ ²	1	V _{CC} = 5V, f = 500MHz	_	- 33	_	dB			
Maximum Output Level	Po	1	$V_{CC} = 5V$, $f = 500MHz$, $Pin = 0dBmW$	_	5	_	dBmW			

Note 1:BW is frequency of 3dB down from $|S_{21}|^2$ at 500MHz.

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TEST CIRCUIT 1

